

L Number	Hits	Search Text	DB	Time stamp
1	2	((("5773088") or ("20020005689")).PN.	USPAT; US-PGPUB	2004/06/13 18:25
3	2	((("20010038099") or ("6458635")).PN.	USPAT; US-PGPUB	2004/06/13 18:33
4	109631	sputter\$3	USPAT; US-PGPUB	2004/06/13 18:34
5	138	"base-coat"	USPAT; US-PGPUB	2004/06/13 18:34
6	30239	"a-si" or "amorphous silicon"	USPAT; US-PGPUB	2004/06/13 18:34
7	0	sputter\$3 with "base-coat"	USPAT; US-PGPUB	2004/06/13 18:34
8	2305	sputter\$3 with ("a-si" or "amorphous silicon")	USPAT; US-PGPUB	2004/06/13 18:35
9	20796	tft	USPAT; US-PGPUB	2004/06/13 18:35
10	888	(sputter\$3 with ("a-si" or "amorphous silicon")) and tft	USPAT; US-PGPUB	2004/06/13 18:35
11	663922	glass	USPAT; US-PGPUB	2004/06/13 18:35
12	10473	sputter\$3 with glass	USPAT; US-PGPUB	2004/06/13 18:35
13	293	((sputter\$3 with ("a-si" or "amorphous silicon")) and tft) and (sputter\$3 with glass)	USPAT; US-PGPUB	2004/06/13 18:36
14	577711	@ad>20010812 @rlad>20010812	USPAT; US-PGPUB	2004/06/13 18:36
15	232	((sputter\$3 with ("a-si" or "amorphous silicon")) and tft) and (sputter\$3 with glass) not (@ad>20010812 @rlad>20010812)	USPAT; US-PGPUB	2004/06/13 18:45
16	281	("a-si" or "amorphous silicon") with sputter\$3 with oxide	USPAT; US-PGPUB	2004/06/13 18:46
17	138	tft and (("a-si" or "amorphous silicon") with sputter\$3 with oxide)	USPAT; US-PGPUB	2004/06/13 18:46
18	105	(tft and (("a-si" or "amorphous silicon") with sputter\$3 with oxide)) not (@ad>20010812 @rlad>20010812)	USPAT; US-PGPUB	2004/06/13 18:47
19	102	((tft and (("a-si" or "amorphous silicon") with sputter\$3 with oxide)) not (@ad>20010812 @rlad>20010812)) and glass	USPAT; US-PGPUB	2004/06/13 18:47
20	28	("a-si" or "amorphous silicon") with sputter\$3 with oxide) with glass	USPAT; US-PGPUB	2004/06/13 18:47
21	23	((("a-si" or "amorphous silicon") with sputter\$3 with oxide) with glass) not (@ad>20010812 @rlad>20010812)	USPAT; US-PGPUB	2004/06/13 18:47
22	3	(US-6506635-\$.did. or (US-20010000011-\$. or US-20010017683-\$.did.	USPAT; US-PGPUB	2004/06/13 19:09
23	28007	steps with chamber	USPAT; US-PGPUB	2004/06/13 19:00
24	95273	sputtering	USPAT; US-PGPUB	2004/06/13 19:00
25	516	(steps with chamber) with sputtering	USPAT; US-PGPUB	2004/06/13 19:00
26	30	((steps with chamber) with sputtering) and ("a-si" or "amorphous silicon") and oxide	USPAT; US-PGPUB	2004/06/13 19:00
27	26	((steps with chamber) with sputtering) and ("a-si" or "amorphous silicon") and oxide) not (@ad>20010812 @rlad>20010812)	USPAT; US-PGPUB	2004/06/13 19:05
28	596147	chamber	USPAT; US-PGPUB	2004/06/13 19:05
29	11	chamber with (("a-si" or "amorphous silicon") with sputter\$3 with oxide)	USPAT; US-PGPUB	2004/06/13 19:05

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30	368	sequential with sputtering	USPAT; US-PGPUB	2004/06/13 19:09
31	4	tft and (sequential with sputtering)	USPAT; US-PGPUB	2004/06/13 19:09
-	65379	438/\$.ccls.	USPAT; US-PGPUB	2004/03/31 19:04
-	0	semiconductor or ic or "integrated circuit" or microelectronic	USPAT; US-PGPUB	2003/05/29 17:11